

HSM88AS

Silicon Schottky Barrier Diode for Balanced Mixer

REJ03G0135-0600Z

(Previous: ADE-208-046E)

Rev.6.00

Nov.06.2003

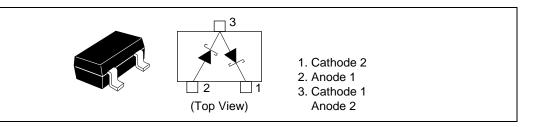
Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSM88AS | C1 | MPAK |

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit | |
|---------------------------|--------|-------------|------|--|
| Reverse voltage | V_R | 10 | V | |
| Average rectified current | lo*1 | 15 | mA | |
| Junction temperature | Tj | 125 | °C | |
| Storage temperature | Tstg | -55 to +125 | °C | |

Note: 1. Per one device

Electrical Characteristics *1

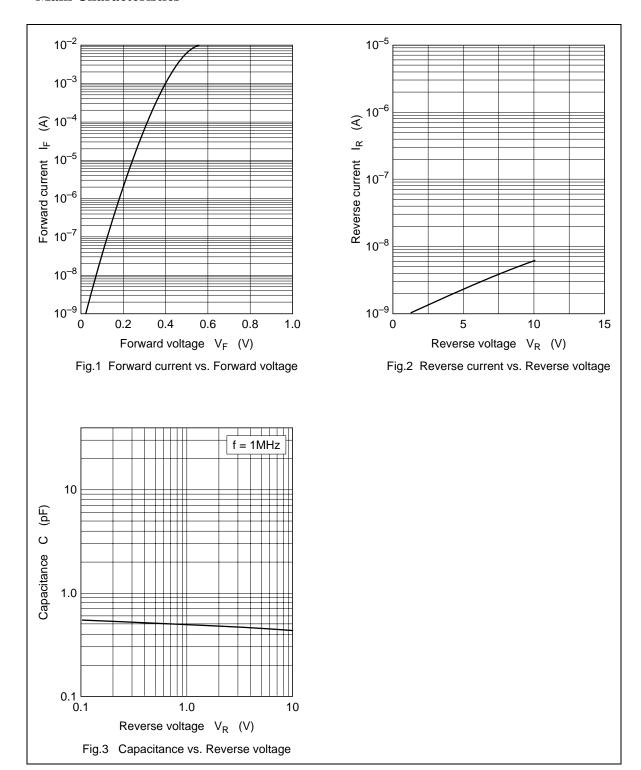
 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|---------------------------|-----------------|------|-----|------|------|--|
| Forward voltage | V_{F1} | 0.35 | _ | 0.42 | V | I _F = 1 mA |
| | V _{F2} | 0.50 | _ | 0.58 | =' | I _F = 10 mA |
| Reverse current | I _{R1} | _ | _ | 0.2 | μΑ | V _R = 2 V |
| | I _{R2} | _ | _ | 10 | =' | V _R = 10 V |
| Capacitance | С | _ | _ | 0.85 | pF | V _R = 0 V, f = 1 MHz |
| Capacitance deviation | ΔC | _ | _ | 0.10 | рF | V _R = 0 V, f = 1 MHz |
| Forward voltage deviation | ΔV_{F} | _ | _ | 10 | mV | I _F = 10 mA |
| ESD-Capability *2 | _ | 30 | _ | _ | V | $C = 200 \text{ pF}, R = 0 \Omega$, Both forward and reverse direction 1 pulse. |

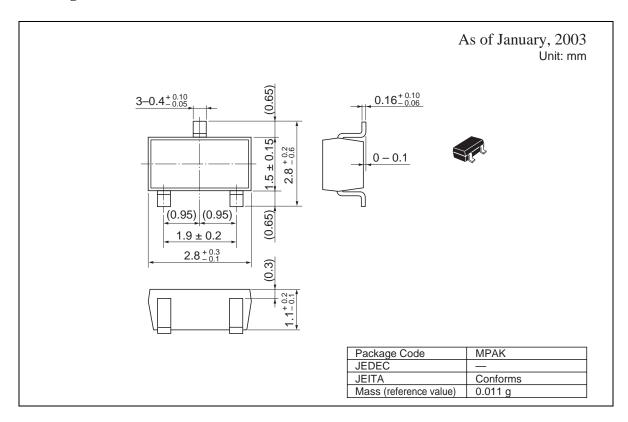
Notes: 1. Per one device

2. Failure criterion ; $I_R \geq 0.4~\mu\text{A}$ at V_R = 2 V

Main Characteristics



Package Dimensions



Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

The pastery in a survival circula designs; and the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.

2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.

The information described here may contain technical inaccuracies or typographical errors.

Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss resident product product of the responsibility of the information of the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).

4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances i

- use.

 6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.

 7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.

 Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

 8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



RENESAS SALES OFFICES

http://www.renesas.com

Renesas Technology America, Inc. 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500 Fax: <1> (408) 382-7501

Renesas Technology Europe Limited.

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, United Kingdom Tel: <44> (1628) 585 100, Fax: <44> (1628) 585 900

Renesas Technology Europe GmbH Dornacher Str. 3, D-85622 Feldkirchen, Germany Tel: <49> (89) 380 70 0, Fax: <49> (89) 929 30 11

Renesas Technology Hong Kong Ltd. 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2375-6836

Renesas Technology Taiwan Co., Ltd. FL 10, #99, Fu-Hsing N. Rd., Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd. 26/F., Ruijin Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001